2025년 2월 14일(금), 15:10-17:10
Room C(컨벤션홀 L), 5층

D. Thin Film Process Technology 분과

O69_[FC3-D] Atomic Layer Deposition - III

좌장: 한정환 교수(서울과학기술대학교), 엄태용 교수(세종대학교)

FC3-D-1 15:10-15:25	**Area-selective Atomic Layer Deposition of Ruthenium Thin Films via Atmospheric Pressure Plasma Technology** Dahui Jeon[1,2] and In-Hwan Baek[1,2] [1]Department of Chemical Engineering, Inha University, [2]Program in Semiconductor Convergence, Inha University
FC3-D-2 15:25-15:40	**Inherent Area-Selective Deposition of Low-resistivity Molybdenum Carbide Films by Thermal Atomic Layer Deposition** Ji Sang Ahn and Jeong Hwan Han Department of Materials Science and Engineering, Seoul National University of Science and Technology
FC3-D-3 15:40-15:55	**Theoretical Development of Area-Selective Atomic Layer Deposition Process of Ruthenium via Reduction of Interfacial Oxidation** Iaan Cho[1],[2], Eun-Hyoung Cho[3], Dabin Kong[4], Youngchul Leem[3], Young Min Lee[3], Miso Kim[1], Chi Thang Nguyen[4], Jeong Yub Lee[3], Han-Bo-Ram Lee[4], and Bonggeun Shong[1] [1]Hongik University, [2]Yonsei University, [3]SAIT, [4]Incheon National University
FC3-D-4 15:55-16:10	**In-Situ Hydrogen Gas Annealing in ALD Reactor for Improved Quality of Cobalt Thin Film** Jaeseong Pyo, Giryun Hong, Jongseo Park, Bohyeon Kang, Jehyun An, Beomjoo Ham, Sung-Min Ahn, and Rock-Hyun Baek Department of Electrical Engineering, POSTECH
FC3-D-5 16:10-16:25	**Development of Atomic Layer Etching of ZrO_2 Thin Films Using NF_3 Plasma and $TiCl_4$** Haram Yang[1], Hyeongjun Kim[2], and Woongkyu Lee[1,2] [1]Department of Materials Science and Engineering, Soongsil University, [2]Department of Green Chemistry and Materials Engineering, Soongsil University

FC3-D-6 16:25-16:40	**Growth Characteristics of ZrO_2, HfO_2, and In_2O_3 Deposited by Liquid Injection Atomic Layer Deposition** Soon-Kyeong Park[1], JunHee Cha[2], and Il-Kwon Oh[1,2] [1]Department of Intelligence Semiconductor Engineering, Ajou University, [2]Department of Electrical and Computer Engineering, Ajou University
FC3-D-7 16:40-16:55	**High Temperature TiN Atomic Layer Deposition Using N-containing Reactants** Hyewon Park, Yoonseo Choi, and Han-Bo-Ram Lee Department of Materials Science and Engineering, Incheon National University
FC3-D-8 16:55-17:10	**Advanced Atomic Layer Deposition: Enhanced Oxidation Resistance and Film Properties of SiN_x Films by Using Highly Reactive N Sources and Discrete Feeding Method** Ui Hyeon You, Jae Chan Park, and Tae Joo Park Department of Materials Science and Chemical Engineering, Hanyang University